

Int'l Appl. No. : PCT/JP2003/016266
Int'l Filing Date : December 18, 2003

AMENDMENTS TO THE SPECIFICATION

Prior to the first line of the specification on page 1, please insert the following paragraph:

This application is the U.S. National Phase under 35 U.S.C. §371 of International Application PCT/JP2003/016266, filed December 18, 2003, which claims priority to Japanese Patent Application No. 2002-376294, filed December 26, 2002. The International Application was not published under PCT Article 21(2) in English.

Please amend the Claims as follows. Insertions are shown underlined while deletions are ~~struck through~~.

The paragraph beginning at page 1, line 13:

KrF positive resist compositions, which have been proposed as ideal resist materials for exposure methods using a KrF excimer laser, typically utilize a polyhydroxystyrene-based resin in which a portion of the hydroxyl groups have been protected with acid dissociable dissolution inhibiting groups as the base resin. As the acid dissociable dissolution inhibiting group, so-called acetal groups including chain-like ether groups typified by 1-ethoxyethyl groups, cyclic ether groups typified by tetrahydropyranyl groups, tertiary alkyl groups typified by tert-butyl groups, and tertiary alkoxycarbonyl groups typified by tert-butoxycarbonyl groups are the most commonly used. See Patent References 1-3 below.

The numeral at page 3, line 4:

{0007}

The numeral at page 4, line 8:

{0013}

The numeral at page 8, line 10:

{0028}

The numeral at page 13, line 19:

{0046}